The Wideband IC Line **RF LDMOS Wideband Integrated Power Amplifier**

The MHVIC2114R2 wideband integrated circuit is designed for base station applications. It uses Motorola's newest High Voltage (26 to 28 Volts) LDMOS IC technology and integrates a multi-stage structure. Its wideband On-Chip matching design makes it usable from 1600 to 2600 MHz. The linearity performances cover all modulation formats for cellular applications: CDMA and W-CDMA. The device is in a PFP-16 flat pack package that provides excellent thermal performance through a solderable backside contact. **Final Application**

Typical Two-Tone Performance: V_{DD} = 27 Volts, I_{DQ1} = 95 mA, I_{DQ2} = 204 mA, I_{DQ3} = 111 mA, P_{out} = 15 Watts PEP, Full Frequency Band Power Gain — 32 dB
 IMD — -30 dBc

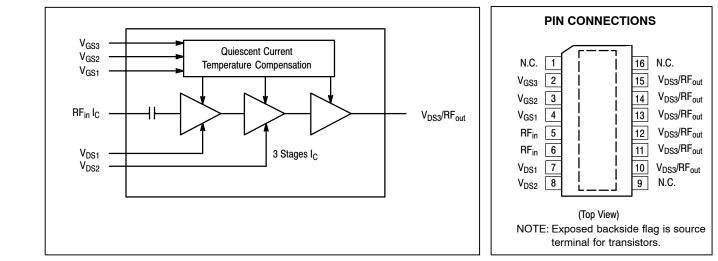
Driver Application

- Typical Single Channel W CDMA Performance: V_{DD} = 27 Volts, I_{DQ1} = 96 mA, I_{DQ2} = 204 mA, I_{DQ3} = 111 mA, P_{out} = 23 dBm, 2110 2170 MHz, 3GPP Test Model 1, Measured in a 3.84 MHz BW @ 5 MHz Offset, 64 DTCH, Peak/Avg. = 8.5 dB @ 0.01% Probability on CCDF. Power Gain 32 dB
 - ACPR -58 dBc
- P1dB = 14 Watts, Gain Flatness = 0.2 dB from 2110 to 2170 MHz
- Capable of Handling 3:1 VSWR, @ 27 Vdc, 2140 MHz, 15 Watts CW Output Power
- Characterized with Series Equivalent Large-Signal Impedance Parameters
 and Common Source Scattering Parameters
- On-Chip Matching (50 Ohm Input, DC Blocked, >5 Ohm Output)
- Integrated Temperature Compensation with Enable/Disable Function
- Integrated ESD Protection
- In Tape and Reel. R2 Suffix = 1,500 Units per 16 mm, 13 inch Reel.



2100 MHz, 27 V, 23 dBm SINGLE W-CDMA RF LDMOS WIDEBAND INTEGRATED POWER AMPLIFIER







MOTOROLA

MAXIMUM RATINGS

Rating		Value	Unit
Drain-Source Voltage	V _{DSS}	65	Vdc
Gate-Source Voltage	V _{GS}	-0.5, +15	Vdc
Storage Temperature Range	T _{stg}	- 65 to +150	°C
Operating Junction Temperature	TJ	150	°C
Input Power	P _{in}	5	dBm

THERMAL CHARACTERISTICS

Characteristic		Symbol	Value (1)	Unit
Thermal Resistance, Junction to) Case	$R_{\theta JC}$		°C/W
Driver Application (P _{out} = +0.2 W CW)	Stage 1, 27 Vdc, I _{DQ1} = 96 mA Stage 2, 27 Vdc, I _{DQ2} = 204 mA Stage 3, 27 Vdc, I _{DQ3} = 111 mA		11.5 7.52 5.52	

ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M1 (Minimum)
Charge Device Model	C2 (Minimum)

MOISTURE SENSITIVITY LEVEL

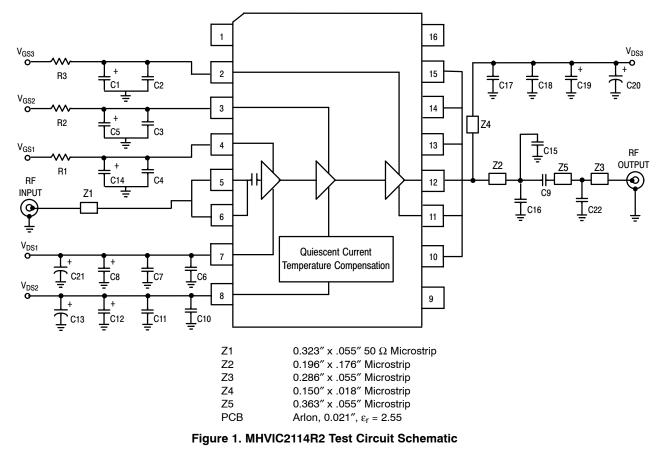
Test Methodology	Rating
Per JESD 22-A113	3

ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
W-CDMA CHARACTERISTICS (In Motorola Test Fixture, 50 ohm system) V _{DD} = 27 Vdc, I _{DQ1} = 96 mA, I _{DQ2} = 204 mA, I _{DQ3} = 111 mA,					
Pout = 23 dBm, 2110-2170 MHz, Single-Carrier W-CDMA, 3.84 MHz Channel Bandwidth Carrier. ACPR measured in 3.84 MHz Channel					
Bandwidth @ \pm 5 MHz Offset. Peak/Avg. = 8.5 dB @ 0.01% Probability on CCDF.					

Power Gain	G _{ps}	29	32	36	dB
Gain Flatness	G _F	_	0.3	0.5	dB
Input Return Loss	IRL	_	-13	-10	dB
Adjacent Channel Power Ratio	ACPR	_	-60	-57	dBc
Group Delay	Delay	_	1.7	—	ns
Phase Linearity	—		0.2	—	0

 Refer to AN1955/D, Thermal Measurement Methodology of RF Power Amplifiers. Go to <u>http://www.motorola.com/semiconductors/rf</u>. Select Documentation/Application Notes - AN1955.



Part	Description	Part Number	Manufacturer
C1, C5, C8, C12, C14, C19	1 µF Tantalum Chip Capacitors	TAJA105K035R	Kemet
C2, C3, C4, C7, C11, C18	0.01 µF Chip Capacitors	0805C103K5RACTR	Vishay
C6, C10, C17	6.8 pF Chip Capacitors (ACCU-P)	AVX08051J6R8BBT	AVX
C9	1.5 pF Chip Capacitor (ACCU-P)	AVX08051J1R5BBT	AVX
C15, C16	2.2 pF Chip Capacitors (ACCU-P)	AVX08051J2R2BBT	AVX
C22	1.0 pF Chip Capacitor (ACCU-P)	AVX08051J1R0BBT	AVX
C13, C20, C21	330 µF Electrolytic Capacitors	MCR35V337M10X16	Multicomp
R1, R2, R3	1 kΩ Chip Resistors (0805)	P1.00KCCT-ND	Panasonic

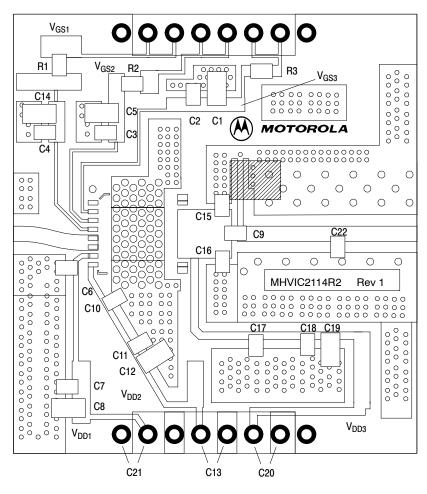


Figure 2. MHVIC2114R2 Test Circuit Component Layout

TYPICAL CHARACTERISTICS

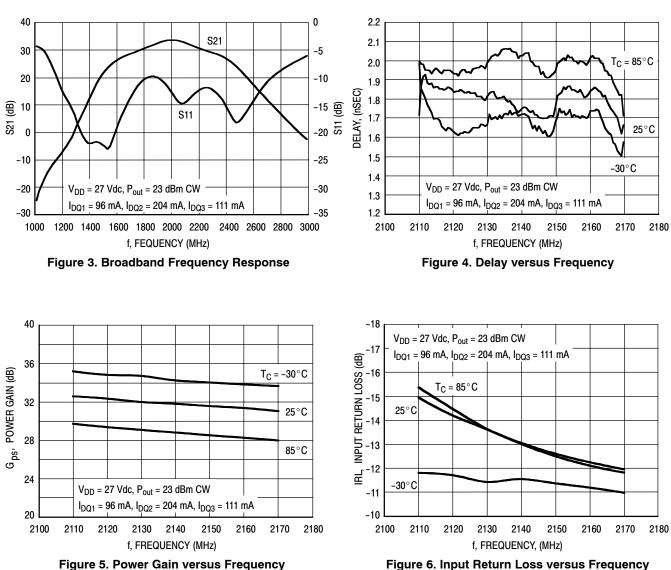
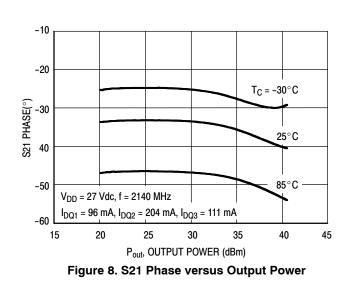


Figure 5. Power Gain versus Frequency



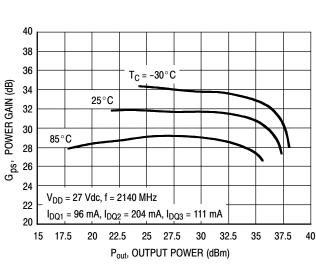


Figure 7. Power Gain versus Output Power

Semiconductor, Inc. Freescale

TYPICAL CHARACTERISTICS

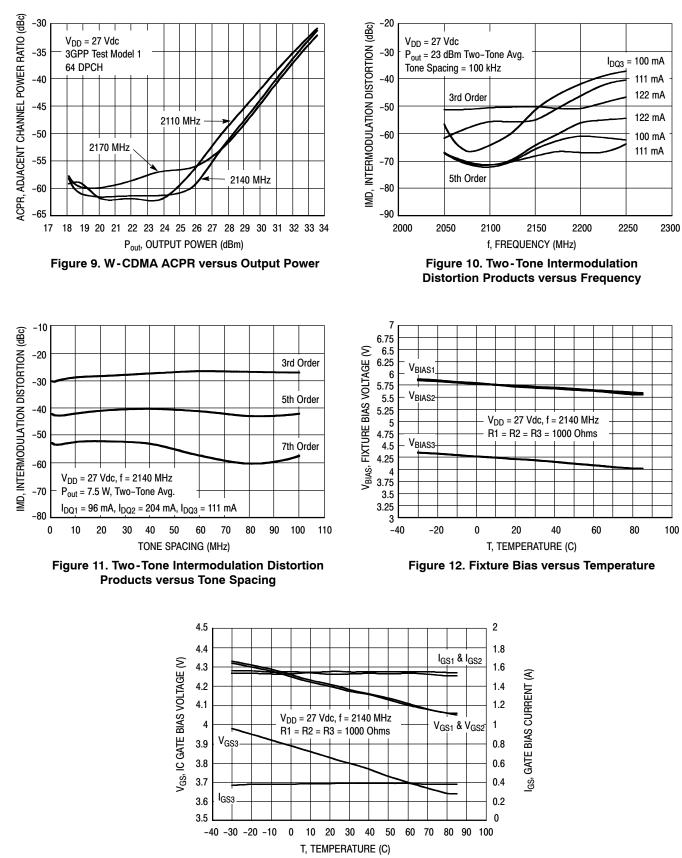
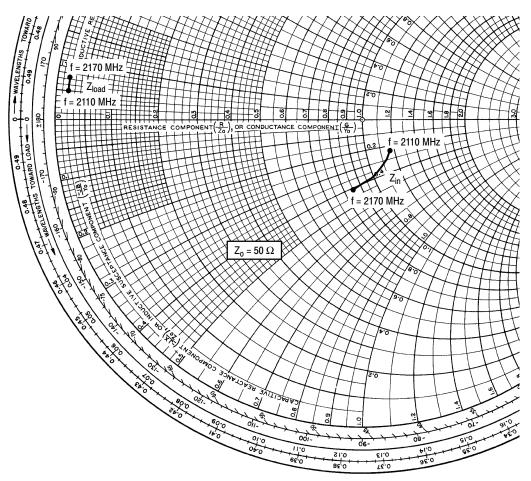


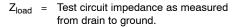
Figure 13. Gate Bias versus Temperature



 V_{DD} = 27 Vdc, I_{DQ1} = 96 mA, I_{DQ2} = 204 mA, I_{DQ3} = 111 mA, P_{out} = 23 dBm

f MHz	Z _{in} Ω	Z_{load}
2110	57.9 - j12.1	1.1 + j2.7
2140	50.6 - j18.9	1.1 + j3.4
2170	42.3 - j21.1	1.2 + j3.7

 Z_{in} = Device input impedance as measured from gate to ground.



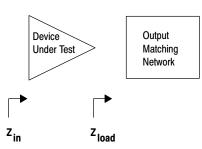
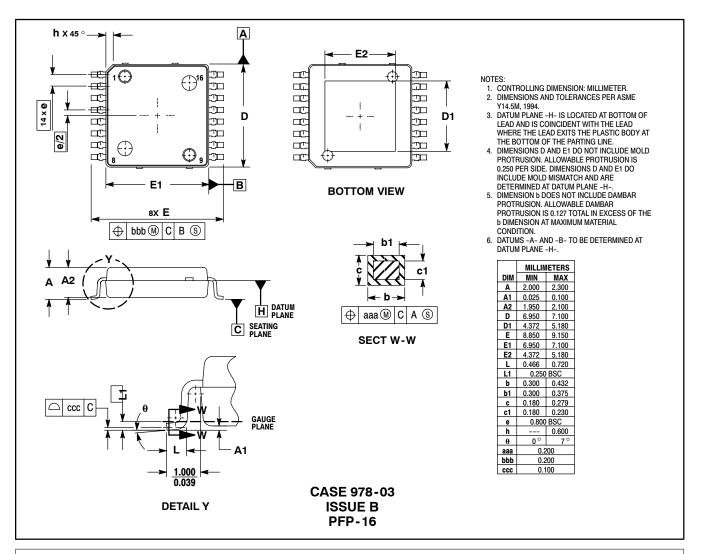


Figure 14. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



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